



STL80N3LLH6

N-channel 30 V, 0.0046 Ω , 21 A PowerFLAT™ 5x6
STripFET™ VI DeepGATE™ Power MOSFET

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D
STL80N3LLH6	30 V	0.0052 Ω	21 A ⁽¹⁾

1. The value is rated according R_{thj-pcb}

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses
- Very low switching gate charge

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

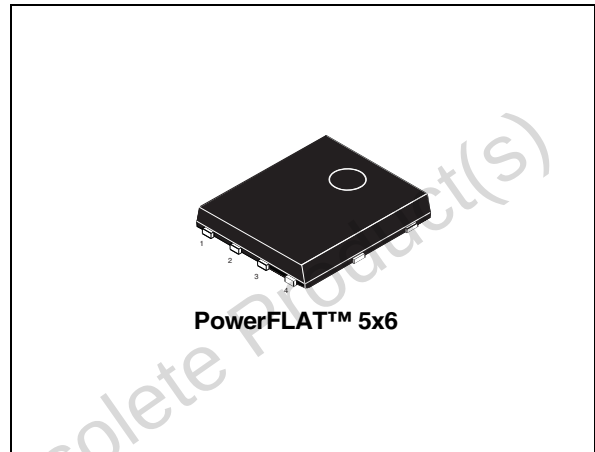


Figure 1. Internal schematic diagram

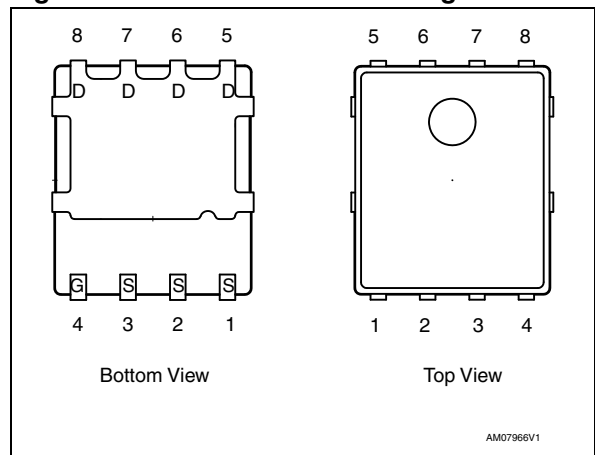


Table 1. Device summary

Order code	Marking	Package	Packaging
STL80N3LLH6	80N3LLH6	PowerFLAT™ 5x6	Tape and reel

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Obsolete Product(s) - Obsolete Product(s)



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 70\text{ }^\circ\text{C}$	60	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	51	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	21	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb}=70\text{ }^\circ\text{C}$	15.7	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb}=100\text{ }^\circ\text{C}$	13.1	A
$I_{DM}^{(3)}$	Drain current (pulsed)	84	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	60	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
T_J	Operating junction temperature	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature		

1. The value is rated according to R_{thj-c} .
2. The value is rated according to $R_{thj-pcb}$.
3. Pulse width limited by safe operating area.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain, steady state)	2.08	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	31.3	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10\text{ sec}$.

2 Electrical characteristics

($T_{CASE} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 30\text{ V}$, $V_{DS} = 30\text{ V}$ at $T_C = 125\text{ }^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1	1.7	2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 10.5\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 10.5\text{ A}$		0.0046 0.0067	0.0052 0.0076	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	1350	1690	2030	pF
C_{oss}	Output capacitance		230	290	350	pF
C_{rss}	Reverse transfer capacitance		140	176	210	pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 21\text{ A}$ $V_{GS} = 4.5\text{ V}$ (see Figure 14)		17		nC
Q_{gs}	Gate-source charge			8		nC
Q_{gd}	Gate-drain charge			6		nC
R_G	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain	1.25	1.7	2	Ω

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$, $I_D=10.5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 13)	-	9.5	-	ns
t_r	Rise time			30		ns
$t_{d(off)}$	Turn-off delay time			37		ns
t_f	Fall time			12		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		21	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		84	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=21\text{ A}$, $V_{GS}=0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD}=10.5\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=25\text{ V}$	-	24		ns
Q_{rr}	Reverse recovery charge			16.8		nC
I_{RRM}	Reverse recovery current			1.4		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

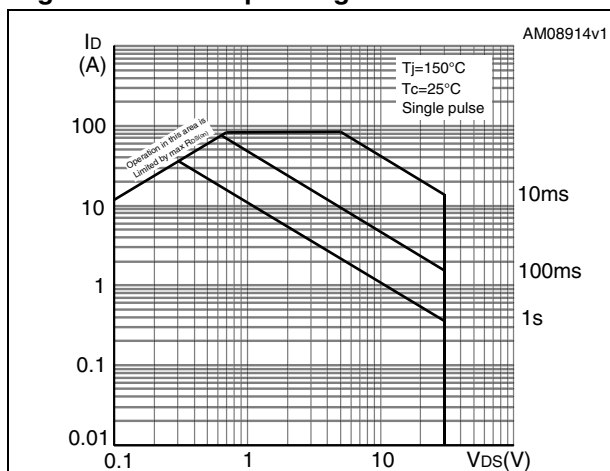


Figure 3. Thermal impedance

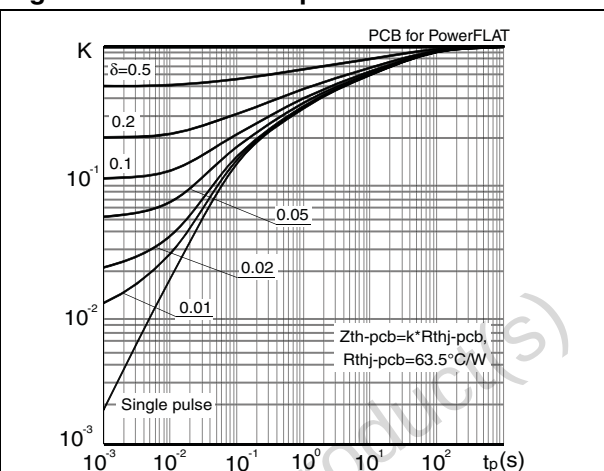


Figure 4. Output characteristics

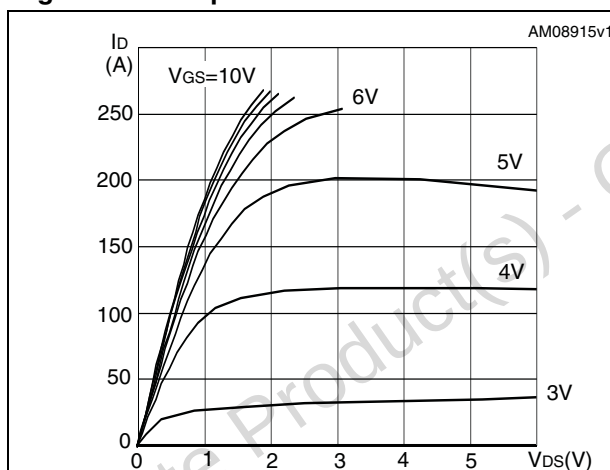


Figure 5. Transfer characteristics

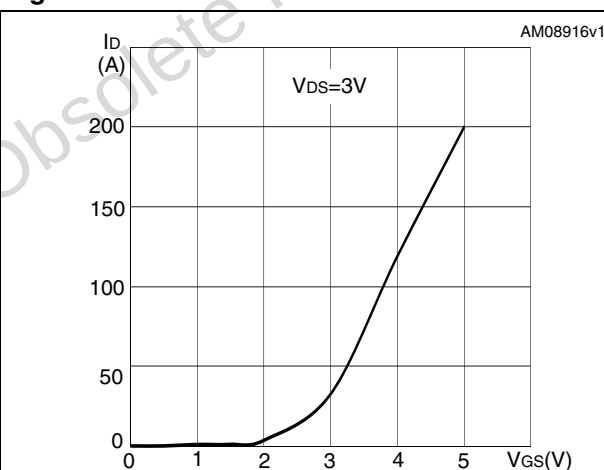
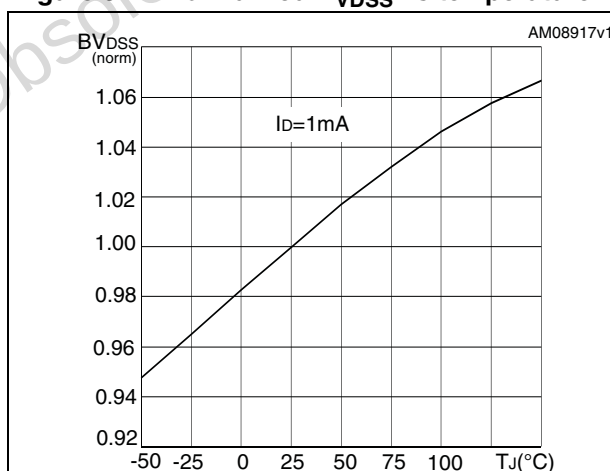
Figure 6. Normalized $B_{V_{DS}}$ vs temperature

Figure 7. Static drain-source on resistance

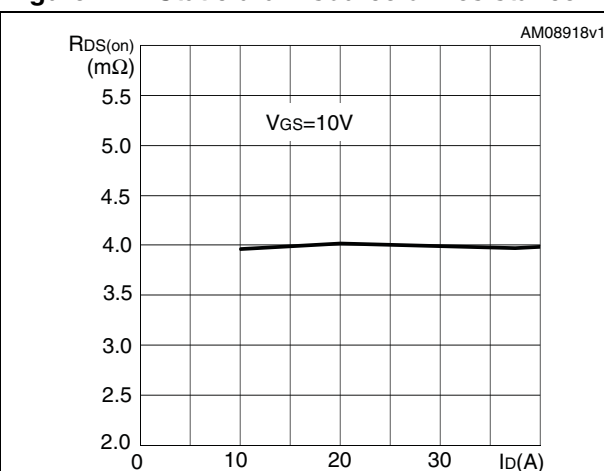


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

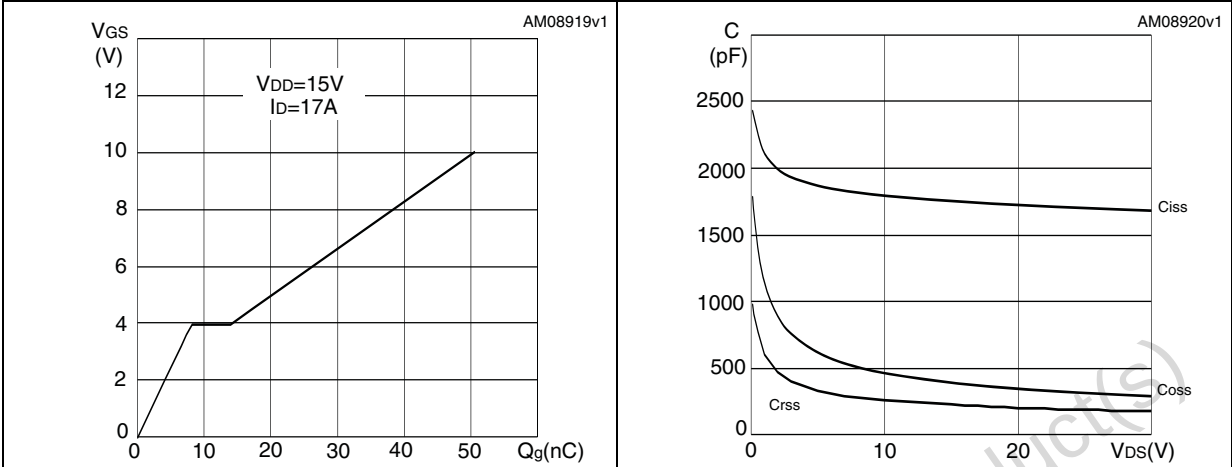


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

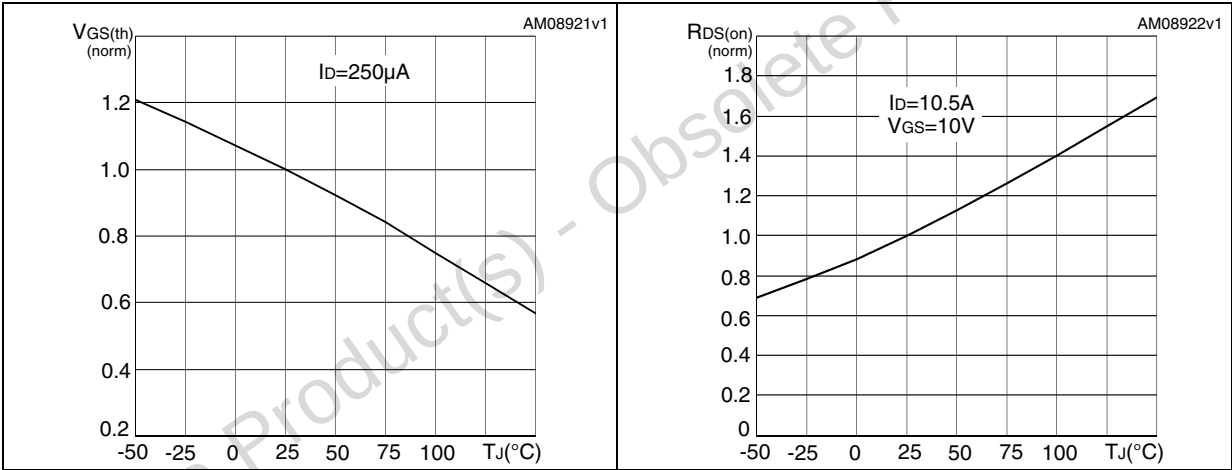
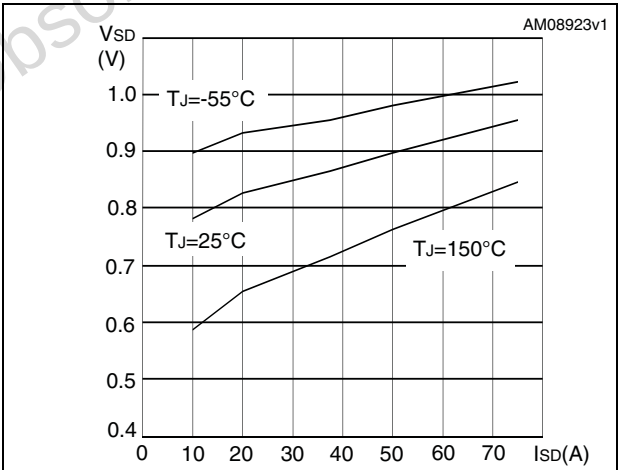


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

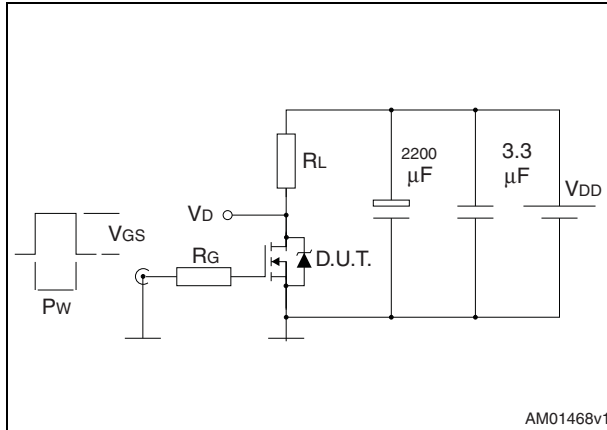


Figure 14. Gate charge test circuit

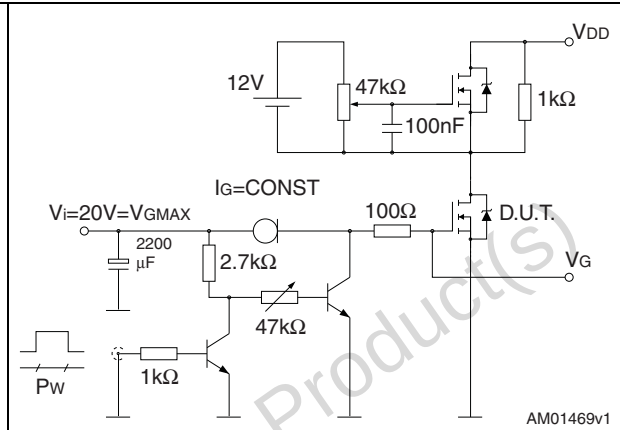


Figure 15. Test circuit for inductive load switching and diode recovery times

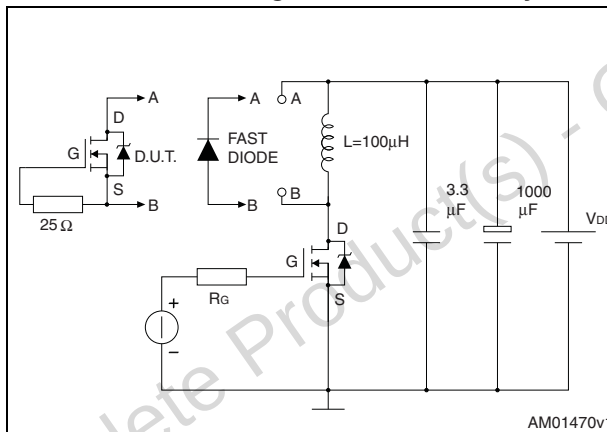


Figure 16. Unclamped inductive load test circuit

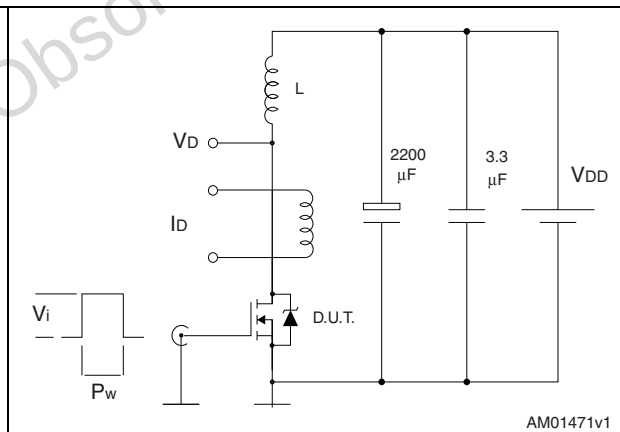


Figure 17. Unclamped inductive waveform

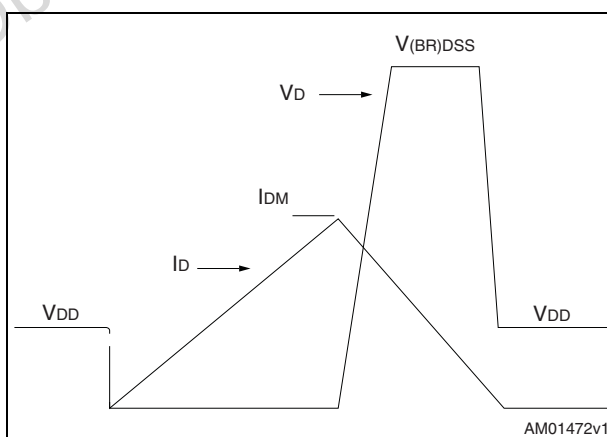
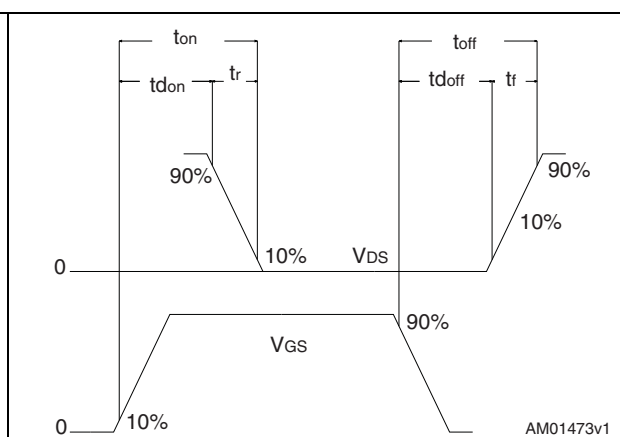


Figure 18. Switching time waveform



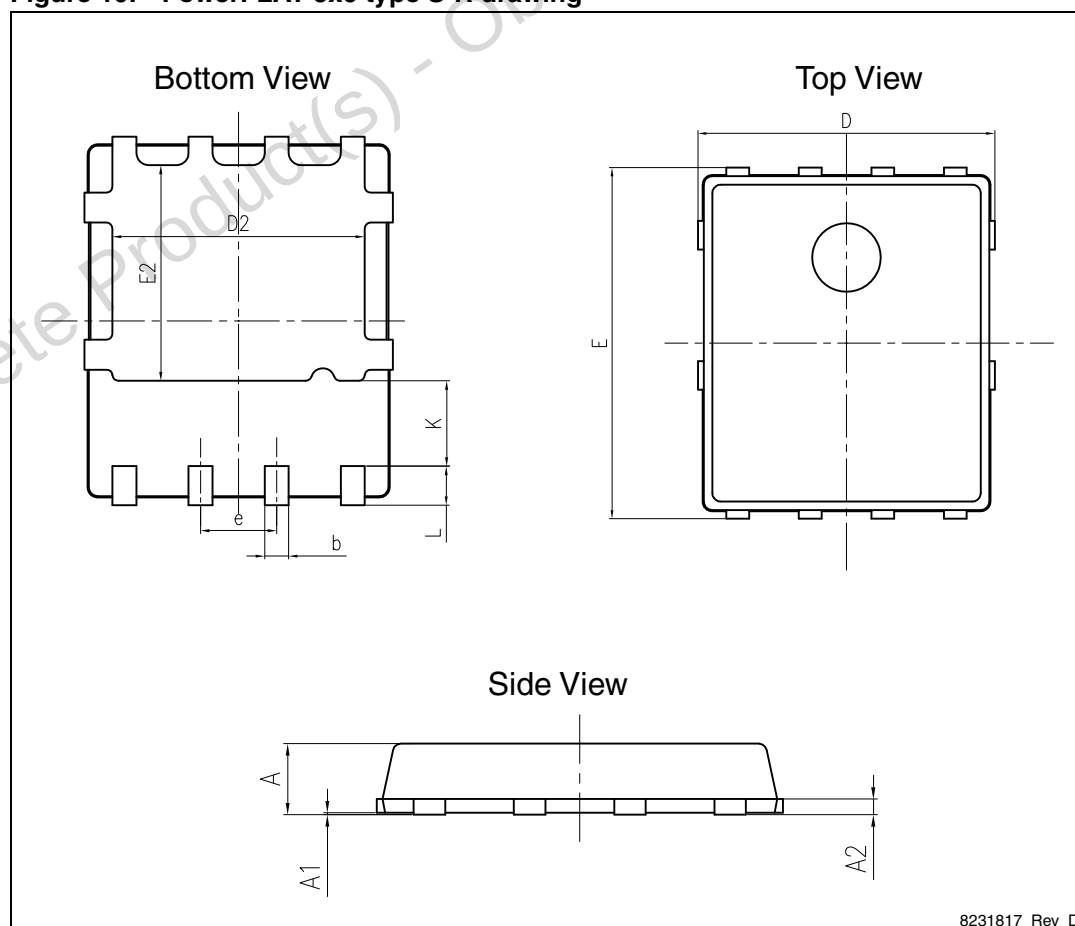
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

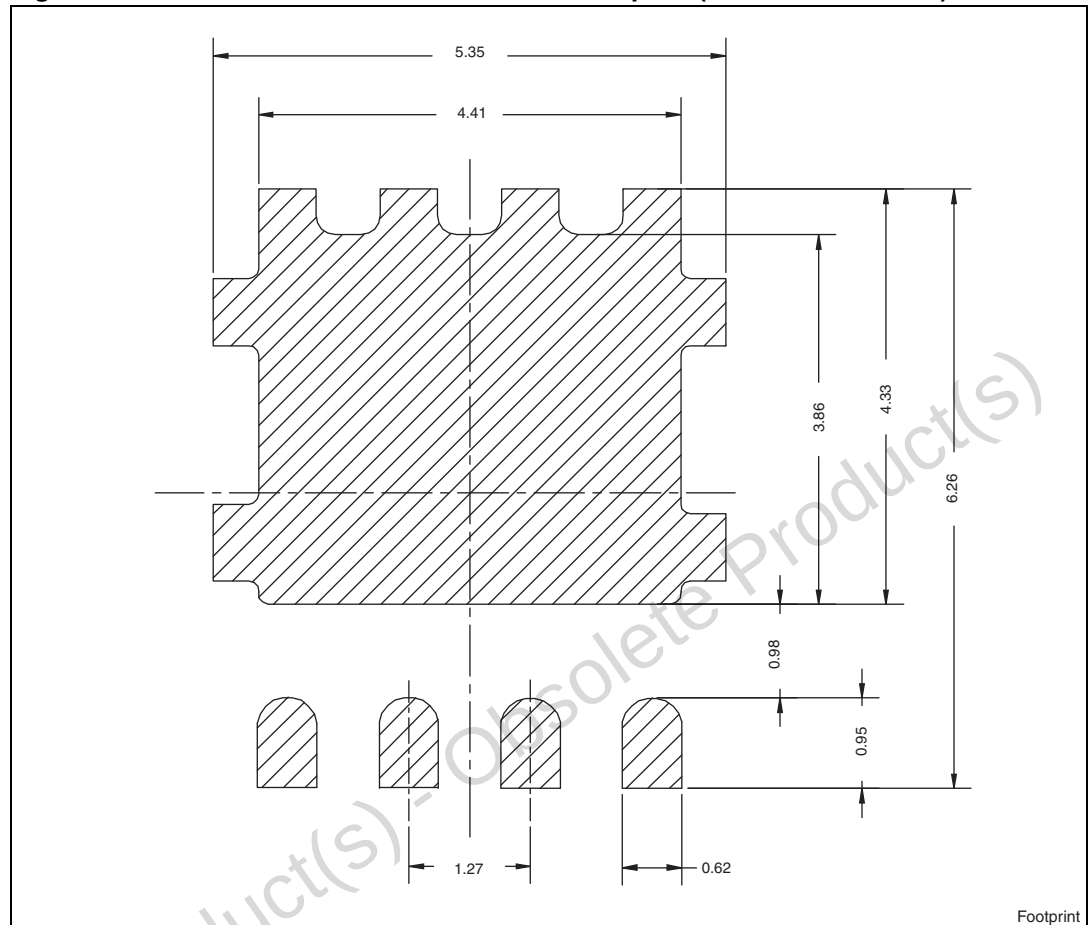
Table 8. PowerFLAT 5x6 type S-R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
L	0.50		0.80
K	1.275		1.575

Figure 19. PowerFLAT 5x6 type S-R drawing

8231817_Rev_D

Figure 20. PowerFLAT™ 5x6 recommended footprint (dimensions in mm)



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
12-Nov-2009	1	First release.
30-Mar-2010	2	$R_{DS(on)}$ values changed in Table 4: On/off states
26-Sep-2011	3	– Document status promoted from preliminary data to datasheet; – Inserted I_D value @ 70 °C, in Table 2: Absolute maximum ratings.
02-Dec-2011	4	Section 4: Package mechanical data has been updated. Minor text changes.

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